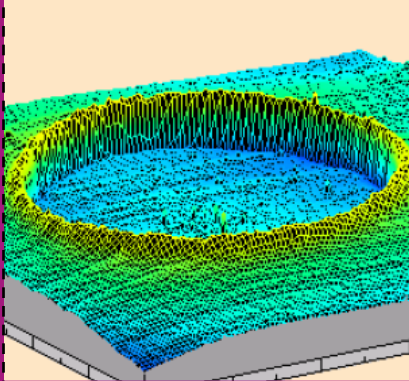


## GD-OES for Depth Profiling



### Simultaneous Multi-Element Analysis of Films and Materials

Balazs™ NanoAnalysis offers the first commercial Glow Discharge Optical Emission Spectroscopy (GD-OES) service in the world. GD-OES profiling capability at single nm resolution has made it a favorite technique of engineers because it provides more than 40 elements in a variety of films and materials. GD-OES is suitable for contamination process control and depth profiling of films and substrates where the elements of interest are not yet identified. GD-OES complements SIMS by providing valuable impurity information in a single elemental survey. It also complements Auger (AES) and ESCA/XPS with its higher detection sensitivity. In addition, GD-OES has a better depth resolution than laser ablation ICP-MS in profiling both conductive and non-conductive films.

#### GD-OES Key Features

- **Simultaneous elemental depth profiling** of more than 40 elements in a single profile with similar depth resolution as SIMS
- **H, C, N, O and S can be detected** that are difficult or impossible to detect by other techniques
- **No charging effect** since GD-OES uses radio frequency (RF) plasma for material sputtering and signal generation; fragile, thermally unstable, conductive and insulating films and materials are readily analyzed without sample modification
- **Large analysis area** of 4 mm improves representative sampling of non-homogeneous materials and films
- **Accurate concentration profiles** can be obtained for major (>5% w/w), minor (0.05 - 5% w/w) and trace elements (<0.05% w/w), due to its wide linear dynamic range.

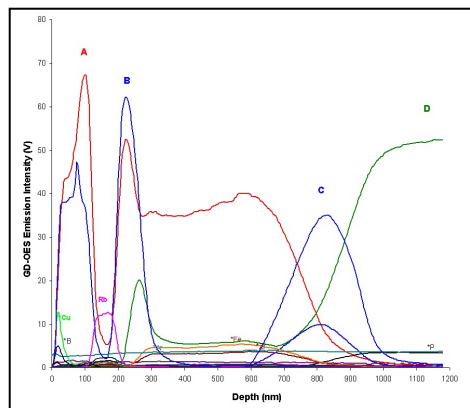


GD-OES instrument

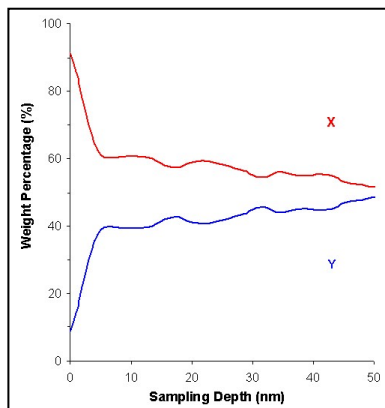
## Film Characterization

Single or multi-layer films are used by a variety of industries.

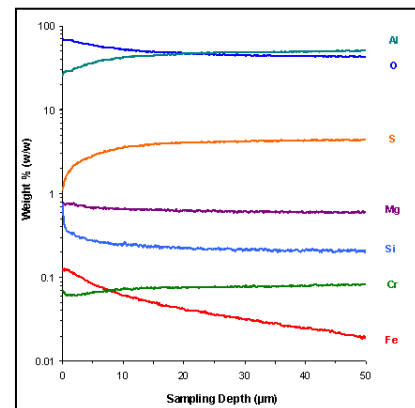
- Corrosion resistance in civic engineering components
- Multi-layer thin film in disk drives
- Anti-reflective coating in optoelectronic optics
- Barrier films in semiconductor devices
- Thin films in photovoltaic cells
- Infrared missile guiding heads in defense



*Simultaneous depth profiling of multi-layer thin films*



*Verification of surface stoichiometry of a solar thin film after a chemical treatment*



*Deep depth profiling anodized alumina coating (ceramic)*

GD-OES provides accurate impurity and compositional analysis with excellent sensitivity, dynamic range and depth resolution making it ideal for

- Lot-to lot variability study of films and materials
- Process reproducibility utilizing its elemental survey capability
- Process development by monitoring more than 40 elements in a single profile
- Process tool cleanliness after preventive maintenance
- Process transfer by surveying simultaneously up to 40 potential cross-contamination elements including H, O, C and N

## Materials R&D

Contamination is a key metric for optimizing film and coating performance. GD-OES and LA ICP-MS are both elemental survey depth profiling techniques that provide cost effective characterization of new materials. The two techniques complement each other in detection limit, sampling area and depth of analysis.

*Table 1. A comparison of GD-OES and LA-ICP-MS*

Technique	Elements Detected	Profiling Mode	Analysis Area	Detection Limit
<b>GD-OES</b>	Periodic table Including H, O, C, N and Cl	Multi-element survey Simultaneous up to 46 elements	4 mm	ppm
<b>LA ICP-MS</b>	Periodic table Except for He, H, F, N, Ar, and O	Multi-element survey Simultaneous up to 85 elements	5 mm	ppm - ppb